

Applications

- DSSS 2.4 GHz WLAN (IEEE802.11b)
- OFDM 2.4 GHz WLAN (IEEE802.11g)
- Access Points, PCMCIA, PC cards

Features

- Single 3.3 V Supply Operation
 - 19 dBm, EVM = 3 %, 802.11g, OFDM 54 Mbps
 - 23 dBm, ACPR < -32 dBc, 802.11b
- 28 dB Gain
- Integrated temperature compensated power detector
- Integrated power amplifier enable pin (V_{EN})
- Lead Free, Halogen Free and RoHS compliant
- Small package: 16 pin 3 mm x 3 mm x 0.9 mm QFN

Product Description

The SE2597L is a 2.4 GHz power amplifier designed for use in the 2.4 GHz ISM band for wireless LAN applications. The device incorporates a power detector for closed loop monitoring of the output power.

The SE2597L includes a digital enable control for device on/off control.

The SE2597L temperature compensated power detector is highly immune to mismatch at its output with less than 1.5 dB of variation with a 2:1 mismatch.

Ordering Information

Part Number	Package	Remark
SE2597L	16 Pin QFN	Samples
SE2597L-R	16 Pin QFN	Tape and Reel
SE2597L-AK1	Application Kit	Standard

Functional Block Diagram

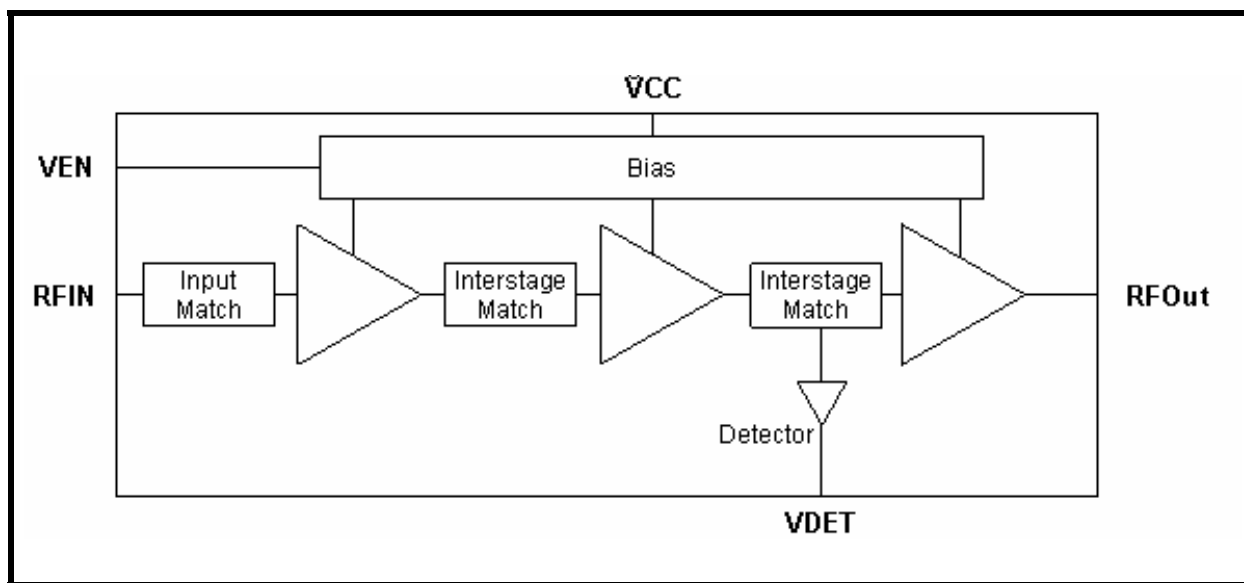


Figure 1: Functional Block Diagram

Pin Out Diagram

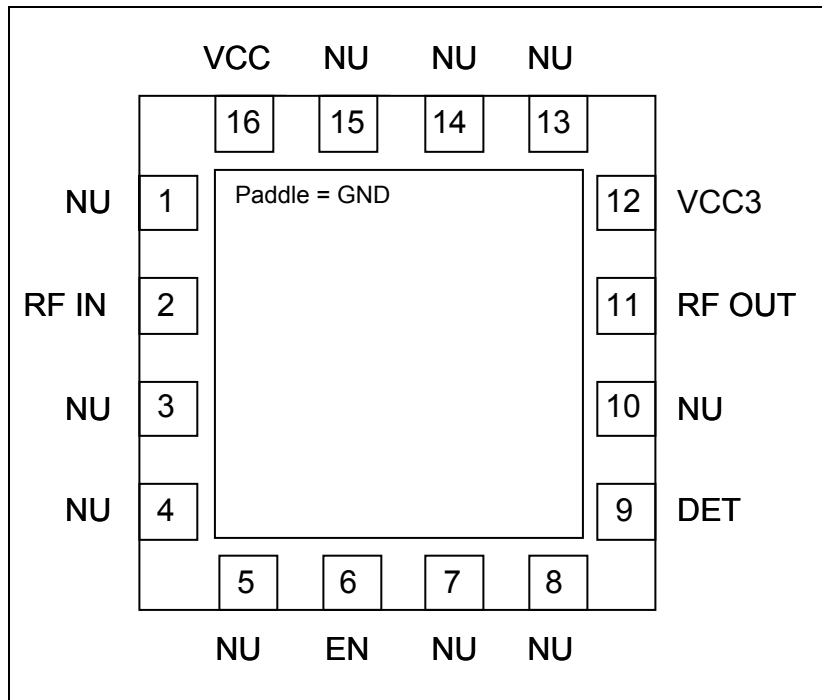


Figure 2: SE2597L Pin-Out Diagram

Pin Out Description

Pin No.	Name	Description
1	NU	No Connect
2	RFin	Power amplifier RF input; DC block required
3,4,5	NU	No Connect
6	EN	Digital pin used to power up and power down the IC
7,8	NU	No Connect
9	DET	Analog power detector output
10	NU	No Connect
11	RFout	Power Amplifier RF output
12	VCC3	Third Stage Collector Voltage
13-15	NU	No Connect
16	VCC	Stages 1, 2 collector supply
Paddle	GND	Exposed die paddle; electrical and thermal ground

Absolute Maximum Ratings

These are stress ratings only. Exposure to stresses beyond these maximum ratings for a long period of time may cause permanent damage to, or affect the reliability of the device. Avoid operating the device outside the recommended operating conditions defined below. This device is ESD sensitive. Handling and assembly of this device should be at ESD protected workstations.

Symbol	Definition	Min.	Max.	Unit
V _{CC}	Supply Voltage on pins V _{CC}	-0.3	4	V
RF _{out}	Supply Voltage on pins V _{CC3} (Note: SE2597L application circuit must be followed for operation above 3.6 V)	-0.3	5.5	V
V _{EN}	Power Amplifier Enable	-0.3	3.6	V
RF _{in}	RF Input Power, RF_OUT terminated into 50Ω match	-	10	dBm
T _{STG}	Storage Temperature Range	-40	150	°C

Recommended Operating Conditions

Symbol	Parameter	Min.	Max.	Unit
V _{CC}	Supply Voltage	3.0	3.6	V
V _{CC3}	Supply Voltage on pins V _{CC3}	3.0	3.6	V
T _A	Ambient Temperature	-20	85	°C

DC Electrical Characteristics

Conditions: V_{CC} = V_{CC3} = V_{EN} = 3.3 V, T_A = 25 °C, as measured on SiGe Semiconductor's SE2597L-EV1 evaluation board, unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _{CC-802.11b}	Supply Current (Sum of V _{CC0} , V _{CC} , V _{CC3})	P _{OUT} = 23 dBm, 11 Mbps CCK signal, BT = 0.45, V _{CC} = V _{CC3} = 3.3 V	-	250	-	mA
I _{CC-802.11g}	Supply Current (Sum of V _{CC} , V _{CC3})	P _{OUT} = 19 dBm, 54 Mbps OFDM signal, 64 QAM, V _{CC} = V _{CC3} = 3.3 V	-	175	-	mA
I _{CQ}	Supply Current (Sum of V _{CC} , V _{CC3})	No RF		125		mA
I _{OFF}	Supply Current	V _{EN} = 0 V, No RF	-	2	10	μA
V _{ENH}	Logic High Voltage	-	1.3	-	V _{CC}	V
V _{ENL}	Logic Low Voltage	-	0	-	0.5	V
I _{ENH}	Input Current Logic High Voltage	-	-	300	-	μA
I _{ENL}	Input Current Logic Low Voltage	-	-	<1	-	μA
Z _{EN}	Enable pin input impedance	Passive Pull Down		10		kΩ

AC Electrical Characteristics

802.11b/g AC Electrical Characteristics

Conditions: $V_{CC} = V_{CC3} = V_{EN} = 3.3\text{ V}$, $f = 2.45\text{ GHz}$, $T_A = 25\text{ }^{\circ}\text{C}$, as measured on SiGe Semiconductor's SE2597L-EV1 evaluation board, unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
f_{L-U}	Frequency Range	-	2400	-	2500	MHz
P_{OUT}	Output Power	54 Mbps OFDM signal, 64 QAM, 3% EVM	-	19	-	dBm
P_{1dB}	Output 1dB compression point	No modulation	24.5	26.5	-	dBm
S_{21}	Small Signal Gain	$P_{IN} = -25\text{ dBm}$	26	28	34	dB
ΔS_{21}	Gain Variation over band	$P_{IN} = -25\text{ dBm}$, $f_{IN} = 2400\text{ to }2500\text{ MHz}$	-	1	-	dB
ACPR	Adjacent Channel Power Ratio $\pm 11\text{ MHz}$ offsets from carrier $\pm 22\text{ MHz}$ offsets from carrier	$P_{OUT} = 23\text{ dBm}$, 11 Mbps CCK signal, BT = 0.45	- -	-33 -52	- -	dBc
2f	Harmonic	$P_{OUT} = 23\text{ dBm}$, CW	-	-50	-	dBm/MHz
3f			-	-50	-	dBm/MHz
t_r, t_f	Rise and Fall Time	-	-	0.5	-	μSec
STAB	Stability	$P_{OUT} = 23\text{ dBm}$, 54 Mbps OFDM signal, 64 QAM VSWR = 6:1 All Phases	All non-harmonically related outputs less than -50 dBc/100 kHz			
VSWR	Tolerance to output load mismatching	$P_{OUT} = 23\text{ dBm}$, 54 Mbps OFDM signal, 64 QAM VSWR = 10:1 All Phases	No damage			

Power Detector

Conditions: $V_{CC} = V_{CC3} = V_{EN} = 3.3\text{ V}$, $f = 2.45\text{ GHz}$, $T_A = 25\text{ }^{\circ}\text{C}$, as measured on SiGe Semiconductor's SE2597L-EV1 evaluation board, unless otherwise noted

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
PDR	P_{OUT} detect range	-	0	-	P_{1dB}	dBm
VDET	Detector voltage	$P_{OUT} = 23\text{ dBm}$	-	1.04	-	V
VDET	Detector voltage	$P_{OUT} = 21\text{ dBm}$	-	0.87	-	V
VDET	Detector voltage	$P_{OUT} = \text{NO RF}$	-	0.33	-	V
PDZ _{OUT}	Output Impedance	-	-	2.3	-	$K\Omega$
PDZ _{LOAD}	DC load impedance	-	10	-	-	$k\Omega$

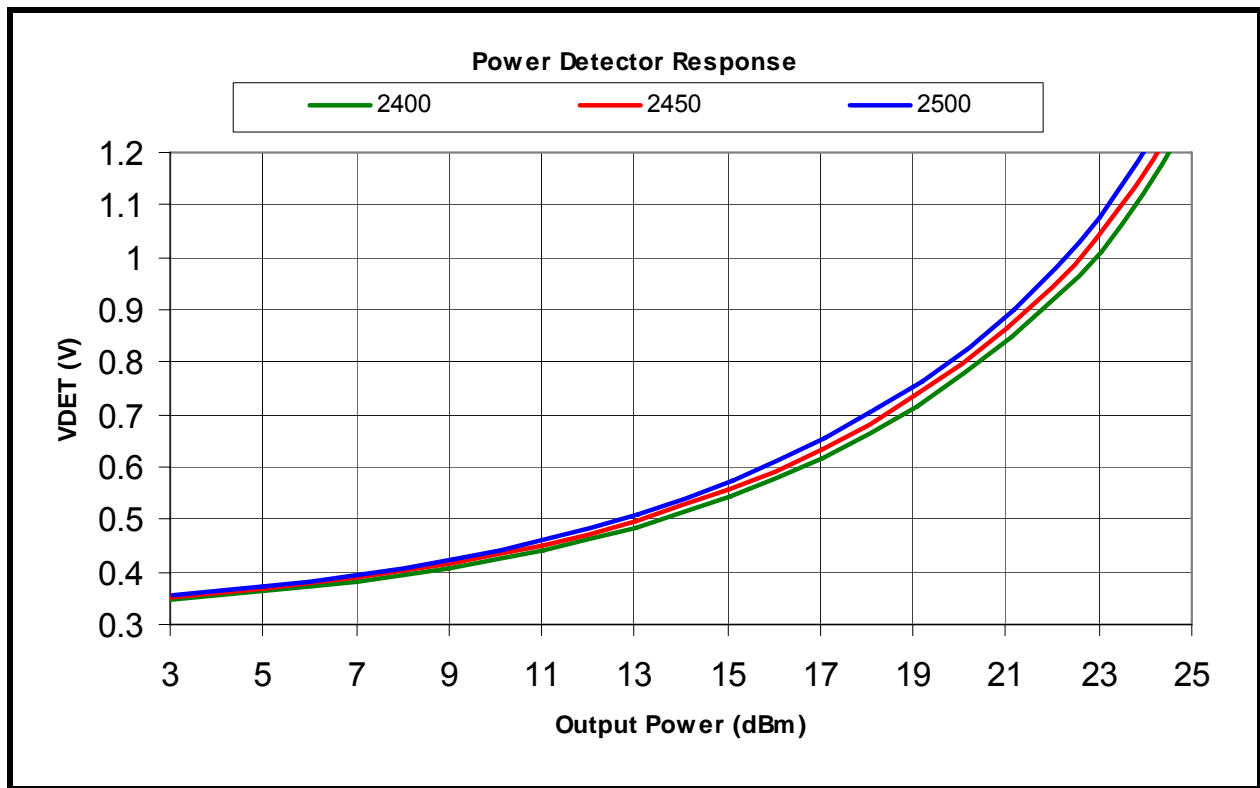


Figure 3: SE2597L Power Detector Characteristic

Package Drawing

This package is Pb free and RoHS compliant. The product is also rated MSL1.

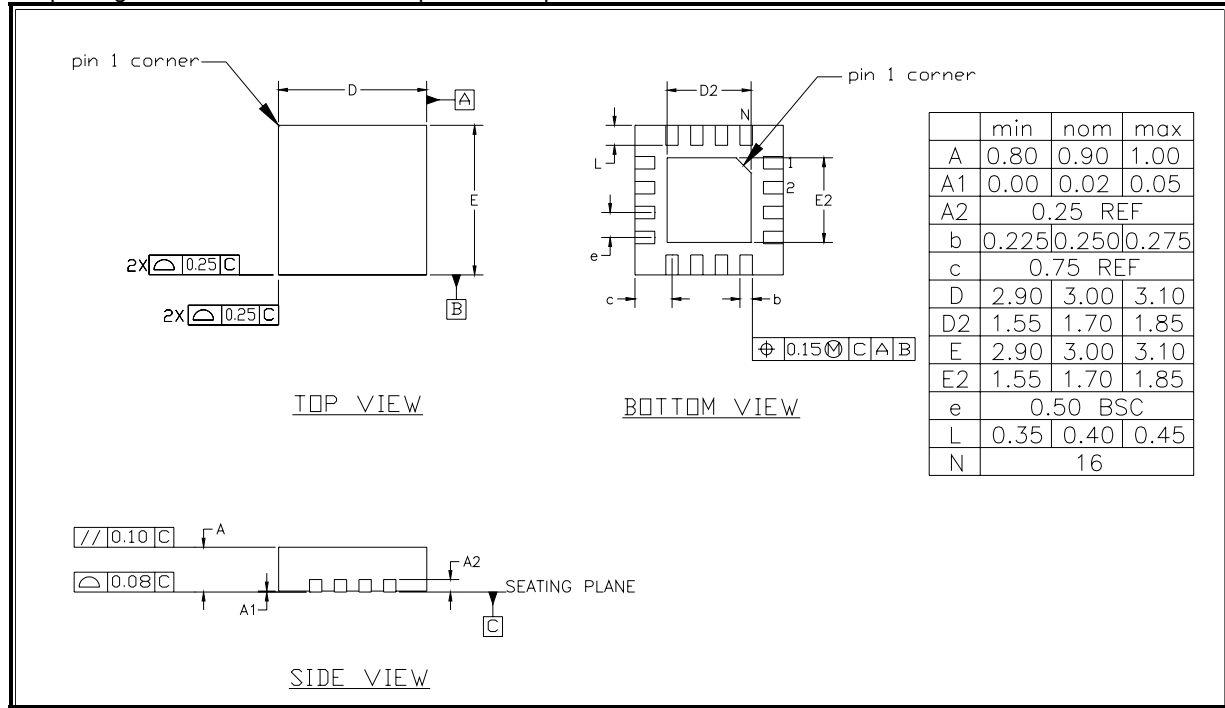


Figure 4: SE2597L Package Drawing: Topside

Recommended Land and Solder Patterns

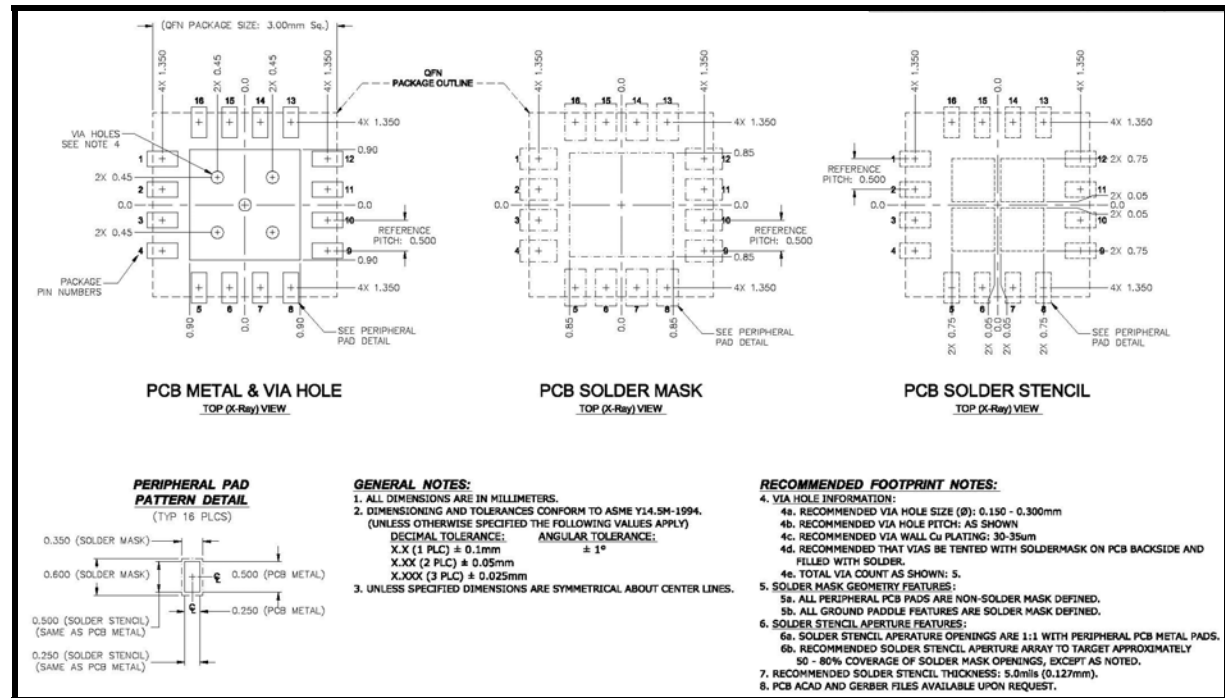


Figure 5: Recommended Land and Solder Patterns

Package Handling Information

Because of its sensitivity to moisture absorption, instructions on the shipping container label must be followed regarding exposure to moisture after the container seal is broken, otherwise, problems related to moisture absorption may occur when the part is subjected to high temperature during solder assembly. The SE2597L is capable of withstanding a Pb free solder reflow. Care must be taken when attaching this product, whether it is done manually or in a production solder reflow environment. If the part is manually attached, precaution should be taken to insure that the device is not subjected to temperatures above its rated peak temperature for an extended period of time. For details on both attachment techniques, precautions, and handling procedures recommended by SiGe, please refer to:

- SiGe's Application Note: "Quad Flat No-Lead Module Solder Reflow & Rework Information", *Document Number QAD-00045*
- SiGe's Application Note: "Handling, Packing, Shipping and Use of Moisture Sensitive QFN", *Document Number QAD-00044*



Caution! Class 0 ESD sensitive device

Branding Information

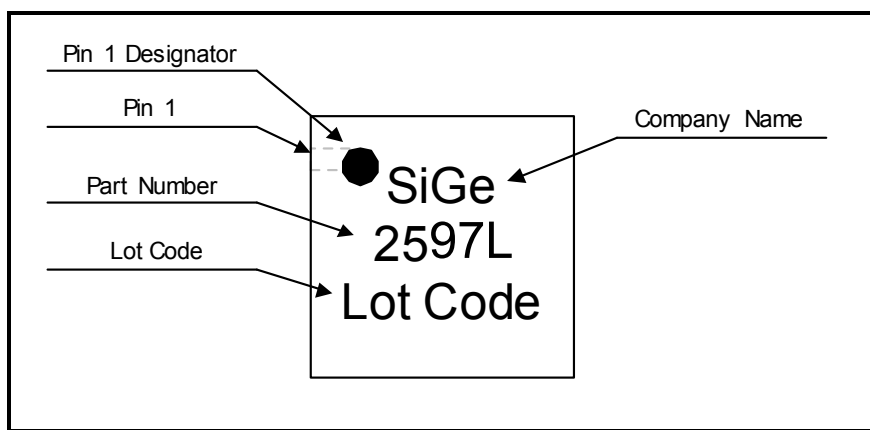


Figure 6: SE2597L Branding Information

Tape and Reel Information

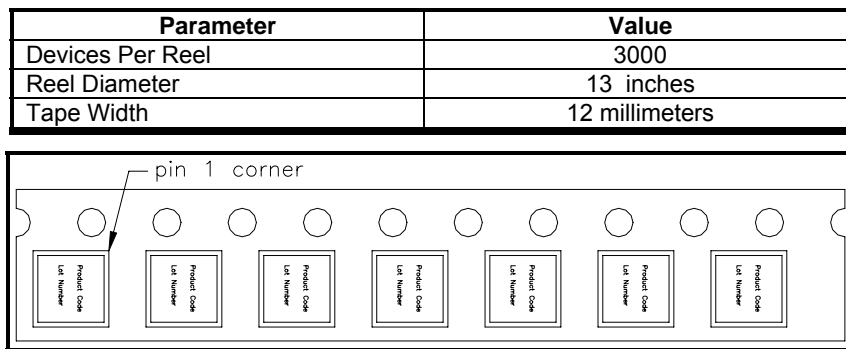


Figure 7: SE2597L-R Tape and Reel Information

Document Change History

Revision	Date	Notes
1.0	May 28, 2008	Created
1.1	Aug 25, 2008	Updated application schematic Added recommended land and solder patterns Updated detector characteristics

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Product Preview

The datasheet contains information from the product concept specification. SiGe Semiconductor, Inc. reserves the right to change information at any time without notification.

Preliminary Information

The datasheet contains information from the design target specification. SiGe Semiconductor, Inc. reserves the right to change information at any time without notification.

Production testing may not include testing of all parameters.

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